



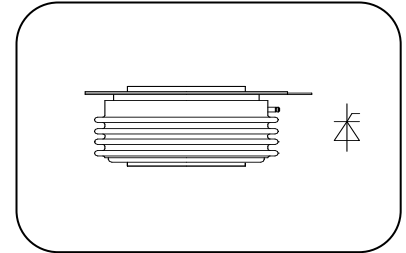
Features:

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses
- Short turn-off time
- Hermetic metal cases with ceramic insulators

Typical Applications

- Inductive heating
- Electronic welders
- Self-commutated inverters
- AC motor speed control
- General power switching applications

$I_{T(AV)}$ **800A**
 V_{DRM}/V_{RRM} **800~1200V**
 t_q **8~14μs**
 I_{TSM} **11kA**



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled, T _c =55°C	125		800	1100	A
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	$V_{DRM} & V_{RRM}, t_p=10ms$ $V_{DSM} & V_{RSM} = V_{DRM} & V_{RRM} + 100V$	125	800		1200	V
I_{DRM} I_{RRM}	Repetitive peak off-state current Repetitive peak reverse current	$V_D = V_{DRM}$ $V_R = V_{RRM}$	125			60	mA
I_{TSM}	Surge on-state current	10ms half sine wave	125			11	kA
I^2t	I ² T for fusing coordination	$V_R = 0.6V_{RRM}$				605	A ² s*10 ³
V_{TO}	Threshold voltage		125			1.41	V
r_T	On-state slop resistance					0.45	mΩ
V_{TM}	Peak on-state voltage	$I_{TM}=2400A, F=21kN$	25			3.2	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			1000	V/μs
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}$ $I_{TM}=(2-3)I_{T(AV)}$, t=5s, Gate pulse t _r ≤ 0.5μs I _{GM} =1.5A f=50Hz	125			600	A/μs
Q _{rr}	Recovery charge	$I_{TM}=1000A, t_p=1000μs,$ di/dt=-20A/μs, V _R =100V	125		63	80	μC
t _q	Circuit commutated turn-off time	$I_{TM}=1000A, t_p=1000μs, V_R=100V$ dv/dt=30V/μs, di/dt=-20A/μs	125	8		14	μs
I _{GT}	Gate trigger current	$V_A=12V, I_A=1A$	25	30		250	mA
V _{GT}	Gate trigger voltage			0.8		3.0	V
I _H	Holding current			20		400	mA
V _{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125			0.3	V
R _{th(j-c)}	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 21kN				0.024	°C /W
R _{th(c-h)}	Thermal resistance case to heat sink					0.006	
F _m	Mounting force			18		25	kN
T _{stg}	Stored temperature			-40		140	°C
W _t	Weight				400		g
Outline	KT50cT						

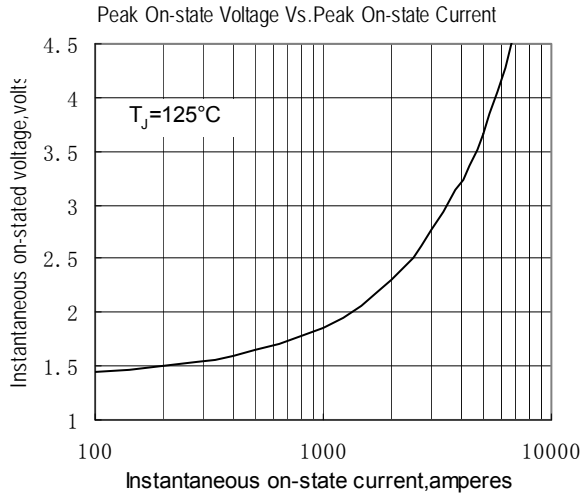


Fig.1

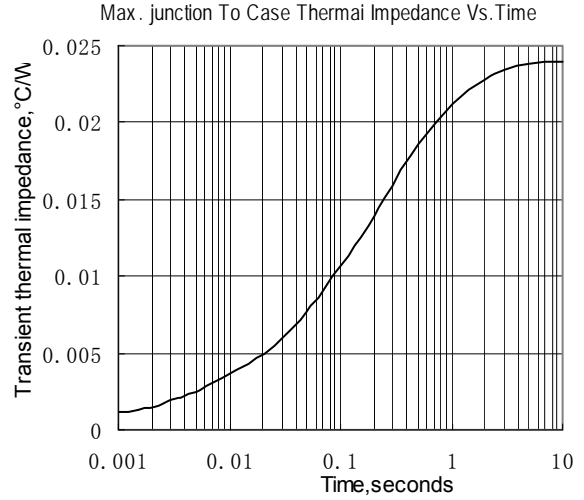


Fig.2

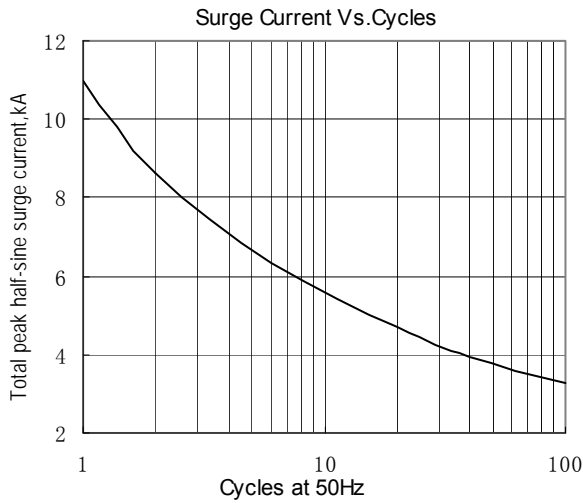


Fig.3

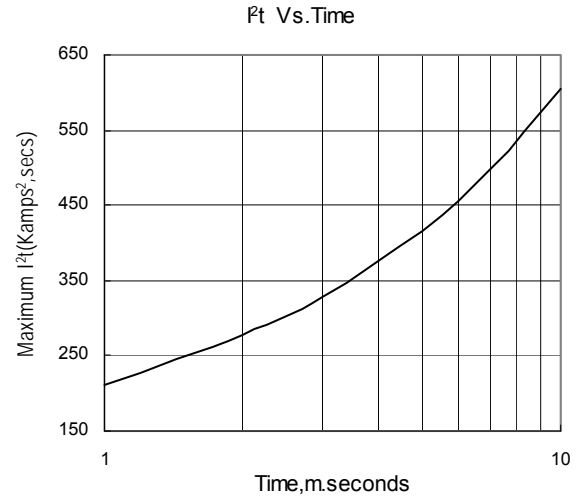


Fig.4

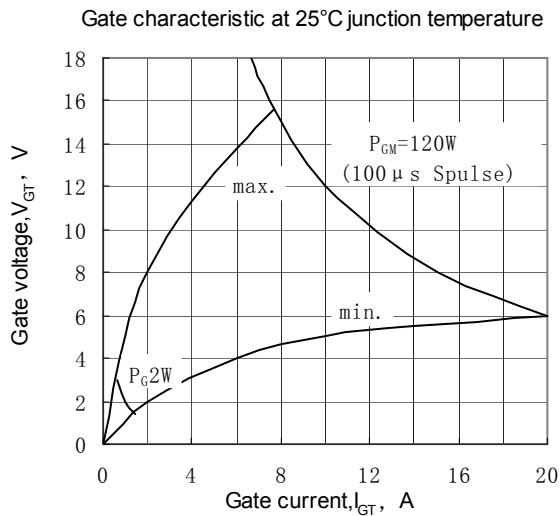


Fig.5

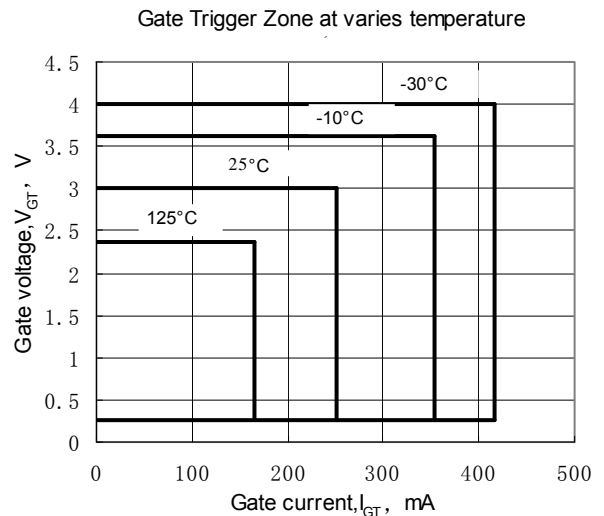
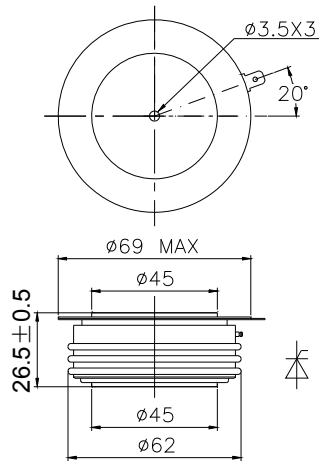


Fig.6



Outline:

图7-KT50cT



地 址 Address: 辽宁省锦州市滨海新区黔江街21号

邮 编 Zipcode: 121007

电 话 Telephone: 0416-2936666 18840127688

传 真 Fax: 0416-2936888

网 址 Web Sit: <http://www.power-semi.com>

电子邮箱 Email: 13904168481@126.com